

Please add new claim 24 as follows:

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--24. (new) A method for manufacturing a semiconductor device comprising:

providing a first region on a semiconductor substrate, the first region including at least one memory cell comprising a MOS transistor and cell capacitor, the cell capacitor including a storage node, a capacitor dielectric layer, and a cell plate;

providing a second region on the semiconductor substrate spaced a distance away from the first region, the second region including an analog element comprising a capacitor element, the capacitor element including a lower electrode, a capacitor dielectric layer, and an upper electrode;

simultaneously forming a storage node for the cell capacitor in the first region and a lower electrode for the capacitor element in the second region by forming a first conducting layer on a dielectric layer extending from the first region into the second region and then etching a portion of the first conducting layer to define the storage node of the cell capacitor in the first region and to define the lower electrode of the capacitor element in the second region;

simultaneously forming a capacitor dielectric layer on the storage node for the cell capacitor in the first region and on the lower electrode in the second region; and

simultaneously forming a second conducting layer on the capacitor dielectric layer on the storage node in the first region to form the cell plate of the cell capacitor and on the capacitor dielectric layer on the lower electrode in the second region to form the upper electrode of the capacitor element.--

Remarks

Applicant has filed an RCE together with this Amendment in response to the Office Action dated Sept. 3, 2002. Claim 16 was amended and claim 24 has been added. Claims 1-8 and 15-24 are currently pending. Reexamination and reconsideration are respectfully requested.

Claim 16 was amended to correct a typographical error as suggested by the Examiner.

Claims 1-8 and 15-23 were rejected under 35 U.S.C. 102(e) as unpatentable over U.S. Patent No. 5,928,959 to Huckels et al. ("Huckels"). The rejection is respectfully traversed.